



WVM3N30(New)

Power MOSFET(N-channel) Transistor



Features:

1. It's voltage control component with good input impedance, small starting power dissipation, wide area of safe operation, good temperature stability.
2. Implementation of standards: GJB33A-97, QZJ840611
3. Use for high speed switch, circuit of power source contravariance.
4. Quality Class: JP, JT, GS, G.

TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications	Test Condition
Drain-Source Voltage	V _{DSS}	V	300(max.)	
Drain Current	I _D	A	3(max.)	
Total Power Dissipation	P _D	W	50(max.)	(Tc=25°C)
Gate-Source Voltage	V _{GSS}	V	±20(max.)	
Junction Temperature	T _{jm}	°C	150	
Storage Temperature	T _{stg}	°C	-55~+150	
Drain-Source Breakdown Voltage	V _{(BR)OSS}	V	Min.:300	V _{GS} =0V, I _D =1Ma
Static Drain-Source On-Resistance	R _{DS(on)}	Ohms	Max.:1.8	V _{GS} =10V, I _D =2A
Gate Threshold Voltage	V _{GS(th)}	V	Min.:2, Max.:4	V _{DS} = V _{GS} , I _D =1Ma
Forward Transconductance	g _{FS}	S	Min.:5	V _{DS} =50V, I _D =1.5A
Zero Gate Voltage Drain Current	I _{DSS}	uA	Max.:1000	V _{GS} =0V, V _{DS} =300V
Gate-Body Leakage	I _{GSS}	nA	Max.:100	V _{GS} =±20V, V _{DS} =0V

Outline and Dimensions: